



flow90PACK 1

1200 V / 15 A

Features

- IGBT M7 with low VCEsat and improved EMC behavior
- Supports designs with 90° mounting angle between heatsink and PCB
- Clip-in PCB mounting

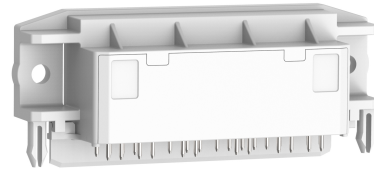
Target applications

- Embedded Drives
- Industrial Drives

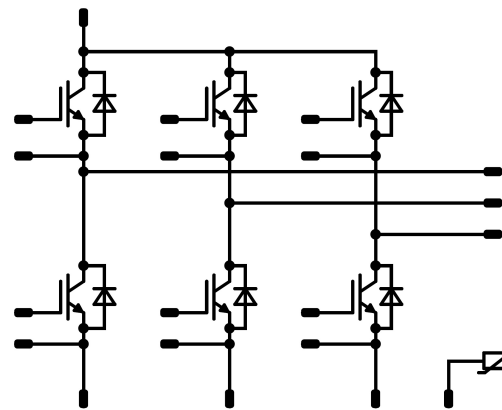
Types

- 10-R1126PA015M7-P708F70

flow90 1 housing



Schematic





Vincotech

10-R1126PA015M7-P708F70
datasheet

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current	I_C	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	21	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	30	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	60	W
Gate-emitter voltage	V_{GES}		± 20	V
Short circuit ratings	i_{SC}	$V_{GE} = 0\text{ V}$, $V_{CC} = 800\text{ V}$ $T_j = 150\text{ °C}$	9,5	μs
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$

Inverter Diode

Peak repetitive reverse voltage	V_{RRM}		1200	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	21	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	30	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	45	W
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$



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10-R1126PA015M7-P708F70
datasheet

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
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Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{jop}		-40...+(T_{jmax} - 25)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	6000	V
Isolation voltage	V_{isol}	AC Voltage $t_p = 1\text{ min}$	2500	V
Creepage distance			min. 12,7	mm
Clearance			11,84	mm
Comparative Tracking Index	CTI		≥ 200	

*100 % tested in production



Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

Inverter Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$			10	0,0015	25	5,4	6	6,6	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		15	25 125 150		1,7 1,95 2,01	2,15	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			60	μA
Gate-emitter leakage current	I_{GES}		0	0		25			500	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}							2900		pF
Output capacitance	C_{oes}		0	10		25		120		pF
Reverse transfer capacitance	C_{res}							34		pF
Gate charge	Q_g	$V_{CC} = 600$ V	15		15	25		110		nC

Thermal

Thermal resistance junction to sink*	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,6		K/W
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*Only valid with pre-applied Vincotech thermal interface material.

Dynamic

Turn-on delay time	$t_{d(on)}$					25 125 150		186 182,6 181,2		ns
Rise time	t_r					25 125 150		37,2 42,6 43,4		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		188,4 211,8 217,6		ns
Fall time	t_f					25 125 150		92,91 119,87 117,17		ns
Turn-on energy (per pulse)	E_{on}	$Q_{rFWD}=1,5$ μC $Q_{rFWD}=2,22$ μC $Q_{rFWD}=2,51$ μC				25 125 150		1,48 1,88 1,99		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		1,01 1,34 1,43		mWs



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

Inverter Diode

Static

Forward voltage	V_F				15	25 125 150		1,62 1,73 1,73	2,1	V
Reverse leakage current	I_R	$V_T = 1200$ V				25			30	μA

Thermal

Thermal resistance junction to sink*	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						2,11		K/W
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*Only valid with pre-applied Vincotech thermal interface material.

Dynamic

Peak recovery current	I_{RRM}					25 125 150		10,77 11,29 11,54		A
Reverse recovery time	t_{rr}					25 125 150		279,38 398,98 443,18		ns
Recovered charge	Q_r	$di/dt=340$ A/μs $di/dt=267$ A/μs $di/dt=281$ A/μs	±15	600	15	25 125 150		1,5 2,22 2,51		μC
Reverse recovered energy	E_{rec}					25 125 150		0,49 0,781 0,899		mWs
Peak rate of fall of recovery current	$(di_{rr}/dt)_{max}$					25 125 150		60,07 50,39 49,15		A/μs



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GS} [V]	V_{GE} [V]	V_{DS} [V]	V_{CE} [V]	T_j [°C]	Min	Typ	Max	

Thermistor

Static

Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$A_{R/R}$	$R_{100} = 1484 \Omega$				100	-5		5	%
Power dissipation	P							5		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. $\pm 1 \%$						3962		K
B-value	$B_{(25/100)}$	Tol. $\pm 1 \%$						4000		K
Vincotech Thermistor Reference									I	

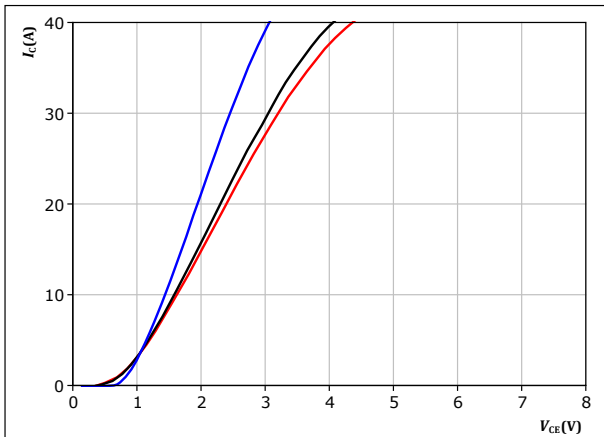


Inverter Switch Characteristics

figure 1. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

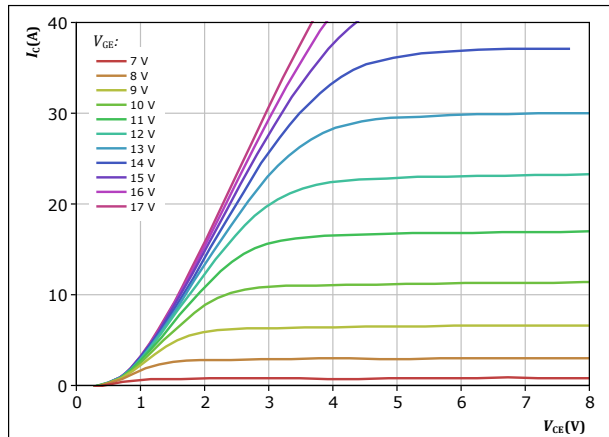


$t_p = 250 \mu s$
 $V_{GE} = 15 V$
 $T_j:$ — 25 °C
— 125 °C
— 150 °C

figure 2. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

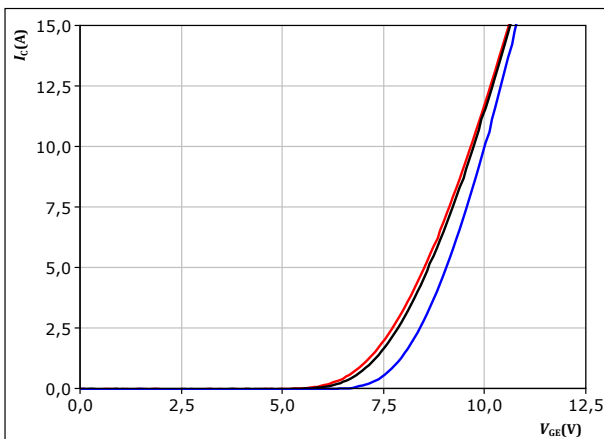


$t_p = 250 \mu s$
 $T_j = 150 \text{ °C}$
 V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

$$I_C = f(V_{GE})$$

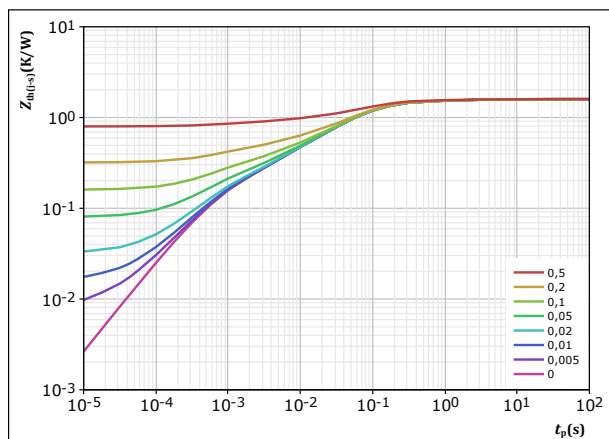


$t_p = 250 \mu s$
 $V_{CE} = 10 V$
 $T_j:$ — 25 °C
— 125 °C
— 150 °C

figure 4. IGBT

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 1,595 \text{ K/W}$
IGBT thermal model values

R (K/W)	τ (s)
4,90E-02	4,40E+00
1,40E-01	5,34E-01
8,04E-01	8,02E-02
2,98E-01	2,57E-02
1,69E-01	5,09E-03
1,35E-01	6,41E-04



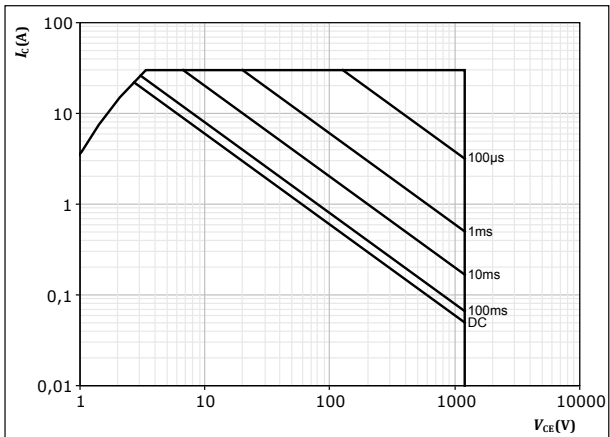
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Inverter Switch Characteristics

figure 5. IGBT

Safe operating area

$$I_C = f(V_{CE})$$



$D =$ single pulse

$T_s = 80$ °C

$V_{GE} = 15$ V

$T_j = T_{jmax}$



Inverter Diode Characteristics

figure 6. FWD

Typical forward characteristics

$$I_F = f(V_F)$$

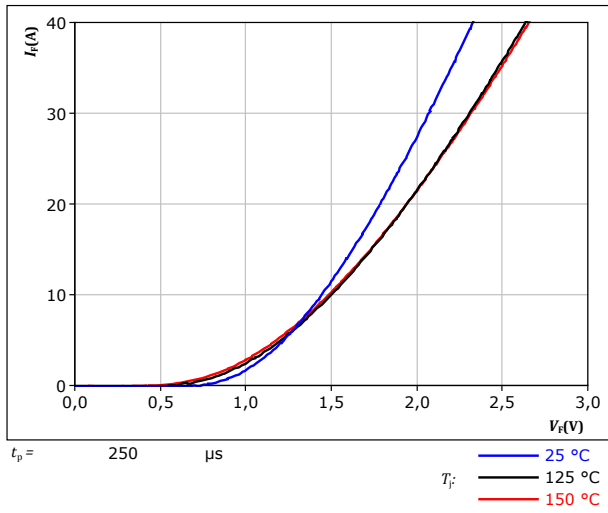
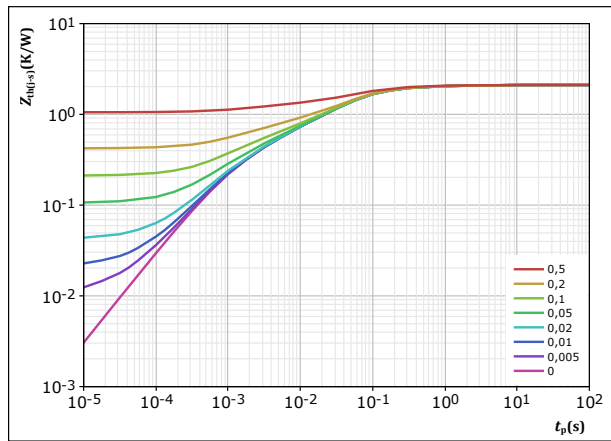


figure 7. FWD

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 2,108$ K/W
 IGBT thermal model values

R (K/W)	τ (s)
8,99E-02	2,33E+00
4,04E-01	1,91E-01
1,05E+00	4,49E-02
3,39E-01	6,08E-03
2,29E-01	1,02E-03

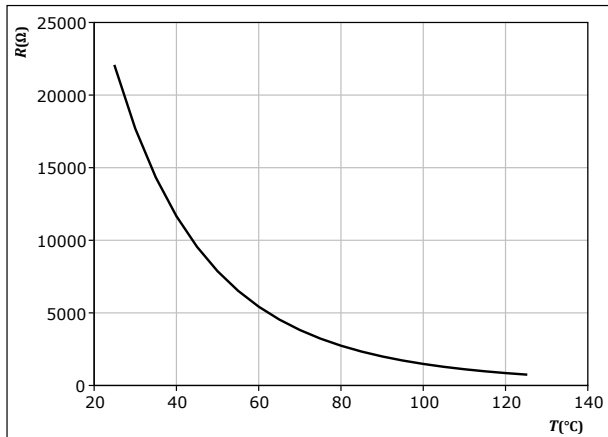


Thermistor Characteristics

figure 8. Thermistor

Typical NTC characteristic as function of temperature

$$R_T = f(T)$$

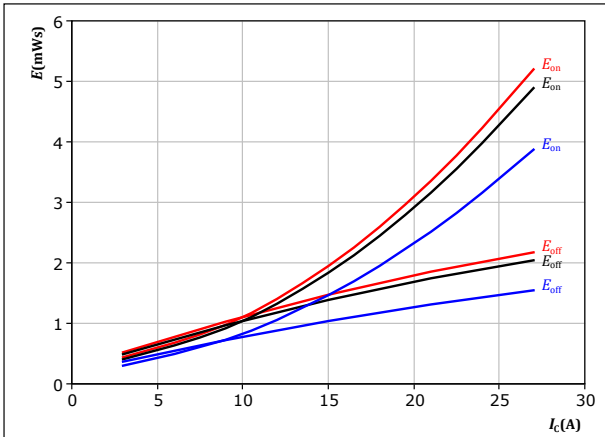




Inverter Switching Characteristics

figure 9. IGBT

Typical switching energy losses as a function of collector current
 $E = f(I_c)$

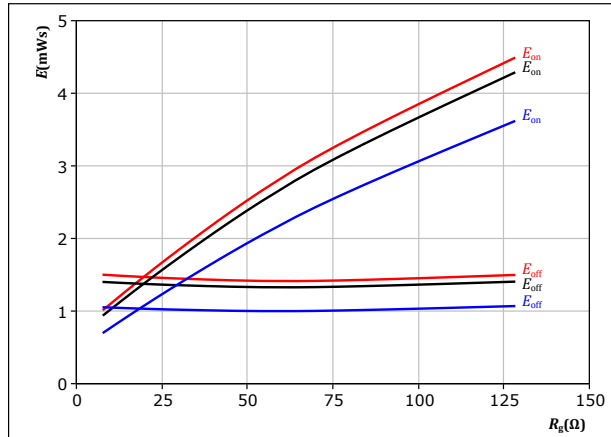


With an inductive load at
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 32$ Ω
 $R_{goff} = 32$ Ω

T_f : — 25 °C
 — 125 °C
 — 150 °C

figure 10. IGBT

Typical switching energy losses as a function of gate resistor
 $E = f(R_g)$

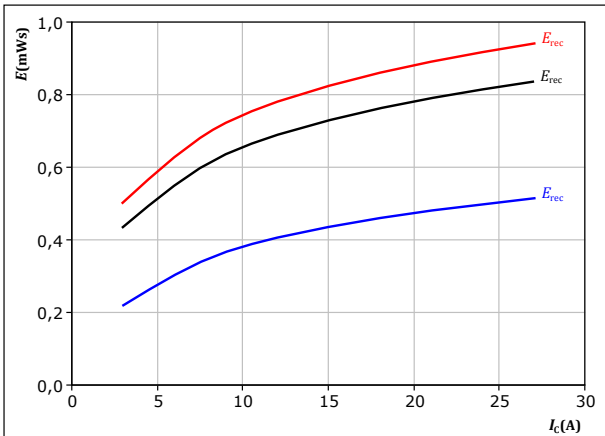


With an inductive load at
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 15$ A

T_f : — 25 °C
 — 125 °C
 — 150 °C

figure 11. FWD

Typical reverse recovered energy loss as a function of collector current
 $E_{rec} = f(I_c)$

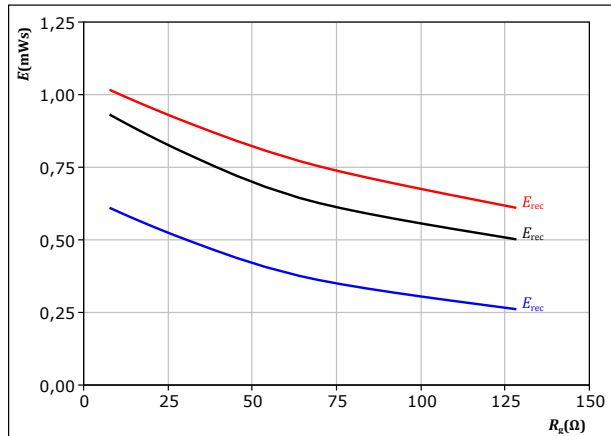


With an inductive load at
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 32$ Ω

T_f : — 25 °C
 — 125 °C
 — 150 °C

figure 12. FWD

Typical reverse recovered energy loss as a function of gate resistor
 $E_{rec} = f(R_g)$



With an inductive load at
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 15$ A

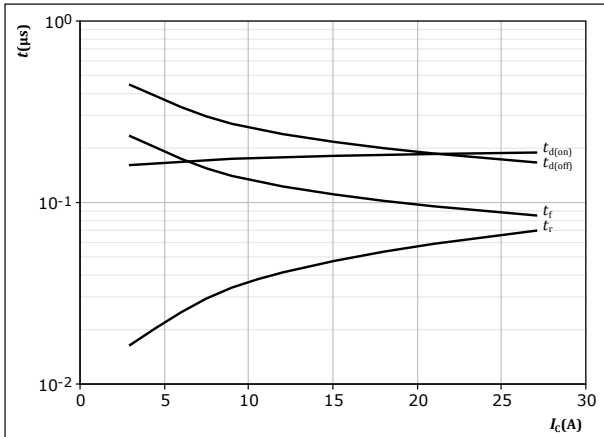
T_f : — 25 °C
 — 125 °C
 — 150 °C



Inverter Switching Characteristics

figure 13. IGBT

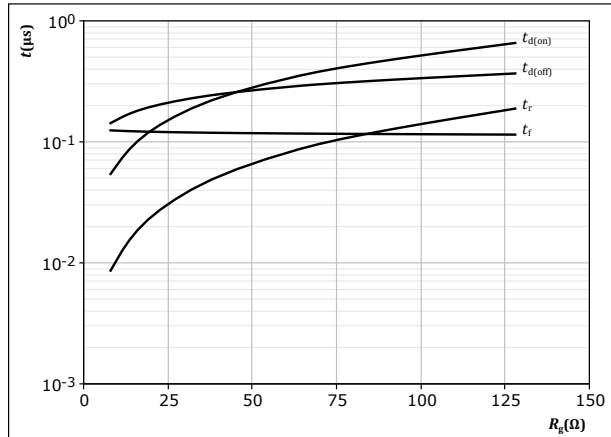
Typical switching times as a function of collector current
 $t = f(I_c)$



With an inductive load at
 $T_j = 150 \text{ }^\circ\text{C}$
 $V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 32 \text{ } \Omega$
 $R_{goff} = 32 \text{ } \Omega$

figure 14. IGBT

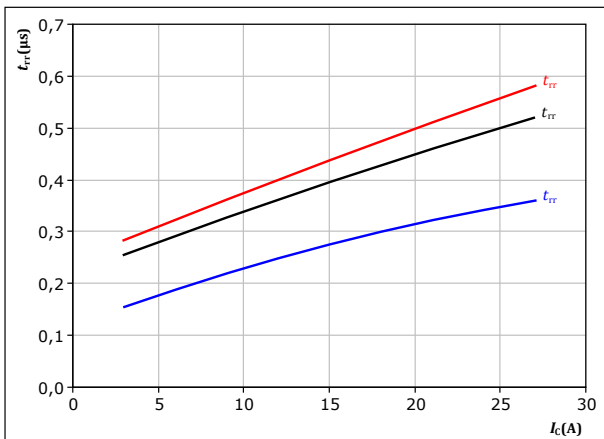
Typical switching times as a function of gate resistor
 $t = f(R_g)$



With an inductive load at
 $T_j = 150 \text{ }^\circ\text{C}$
 $V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_c = 15 \text{ A}$

figure 15. FWD

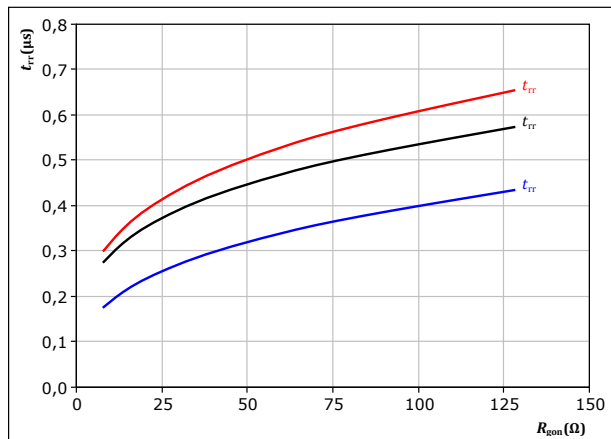
Typical reverse recovery time as a function of collector current
 $t_{rr} = f(I_c)$



With an inductive load at
 $V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 32 \text{ } \Omega$
 $T_j:$ — 25 °C
— 125 °C
— 150 °C

figure 16. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor
 $t_{rr} = f(R_{gon})$



With an inductive load at
 $V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_c = 15 \text{ A}$
 $T_j:$ — 25 °C
— 125 °C
— 150 °C

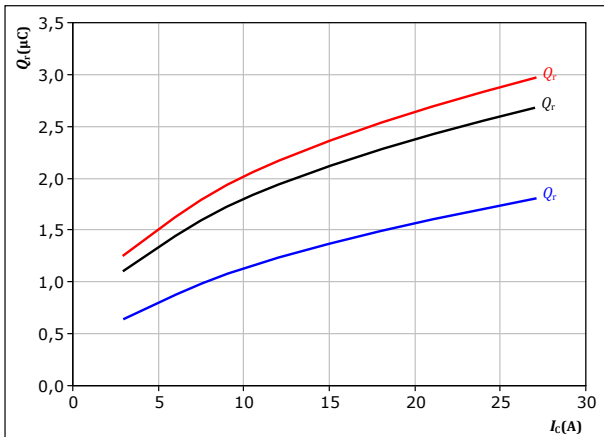


Inverter Switching Characteristics

figure 17. FWD

Typical recovered charge as a function of collector current

$$Q_r = f(I_c)$$



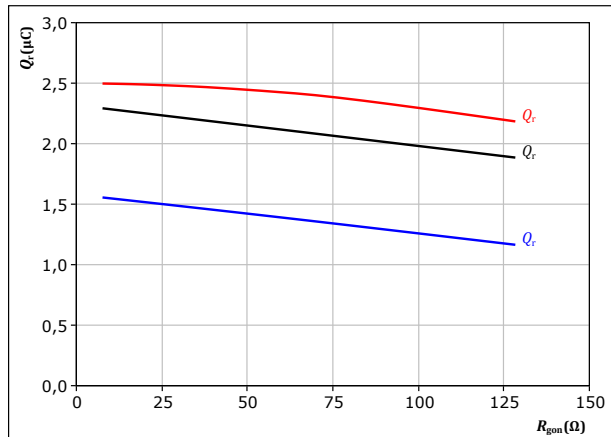
With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 32$ Ω
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 18. FWD

Typical recovered charge as a function of turn on gate resistor

$$Q_r = f(R_{gon})$$



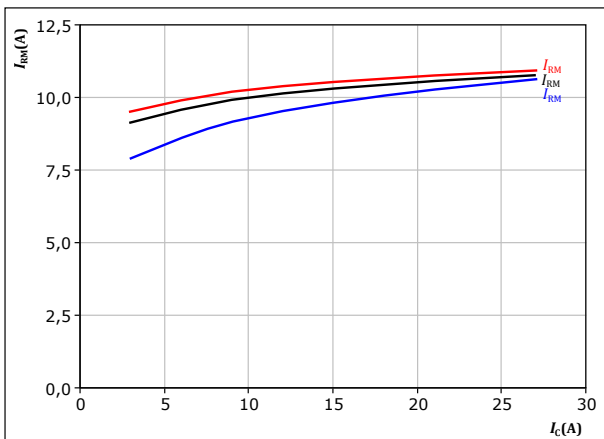
With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 15$ A
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 19. FWD

Typical peak reverse recovery current as a function of collector current

$$I_{RM} = f(I_c)$$



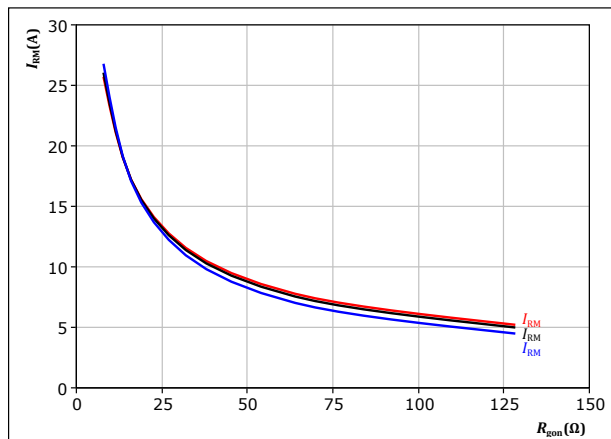
With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 32$ Ω
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 20. FWD

Typical peak reverse recovery current as a function of turn on gate resistor

$$I_{RM} = f(R_{gon})$$



With an inductive load at

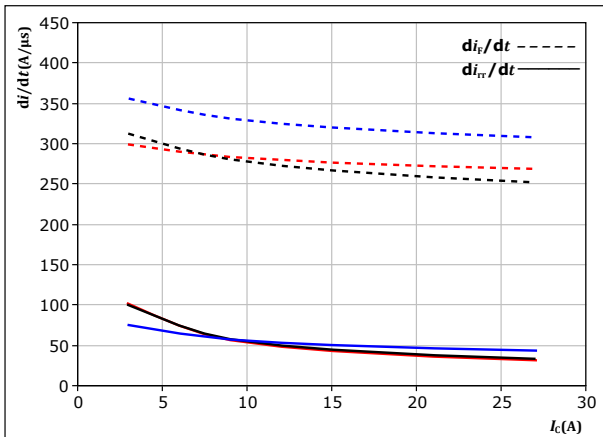
$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 15$ A
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)



Inverter Switching Characteristics

figure 21. FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current
 $di_f/dt, di_r/dt = f(I_c)$



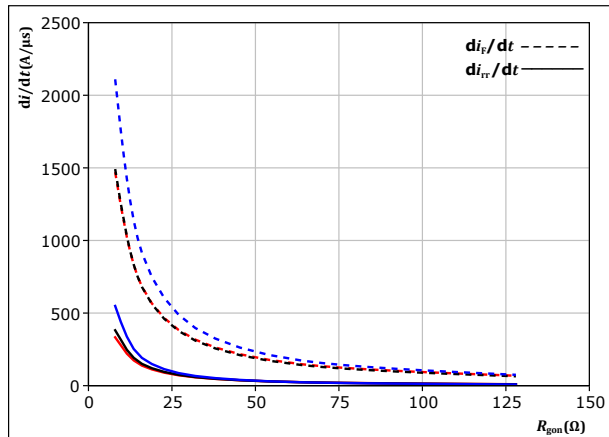
With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 32 \ \Omega$

T_j :
— 25 °C
— 125 °C
— 150 °C

figure 22. FWD

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_r/dt = f(R_{gon})$



With an inductive load at

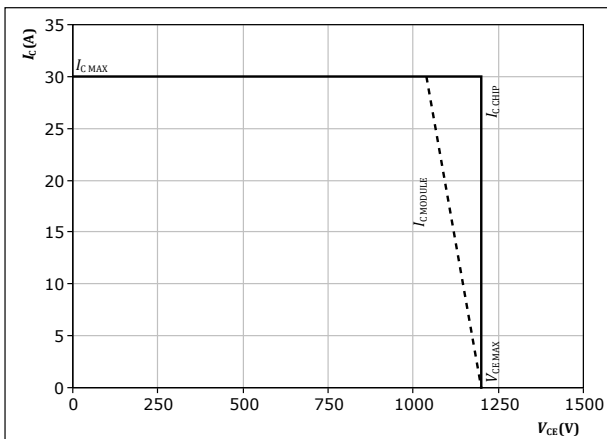
$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_c = 15 \text{ A}$

T_j :
— 25 °C
— 125 °C
— 150 °C

figure 23. IGBT

Reverse bias safe operating area

$I_c = f(V_{CE})$



At $T_j = 150 \text{ °C}$
 $R_{gon} = 32 \ \Omega$
 $R_{goff} = 32 \ \Omega$



Inverter Switching Definitions

figure 24. IGBT
Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})

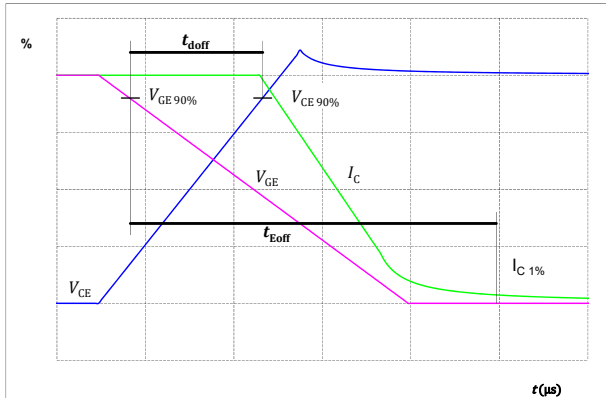


figure 25. IGBT
Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})

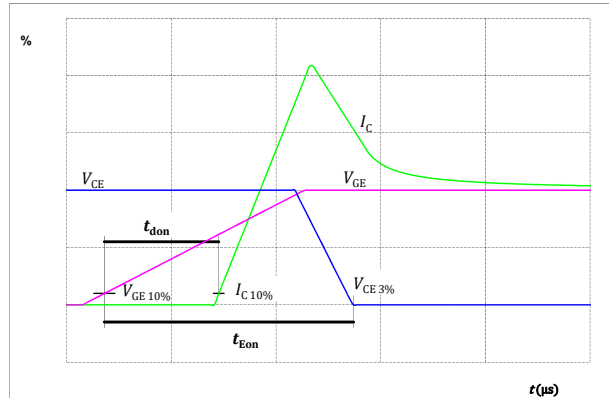


figure 26. IGBT
Turn-off Switching Waveforms & definition of t_f

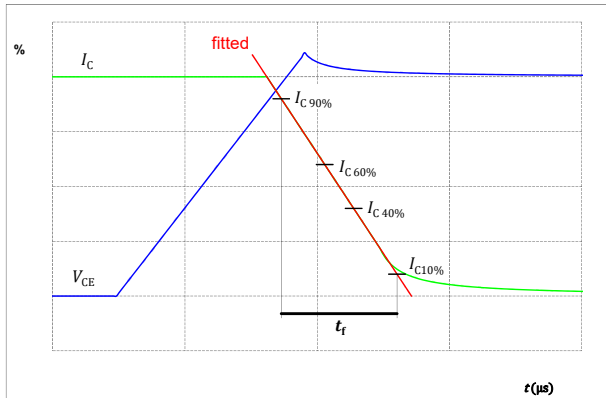
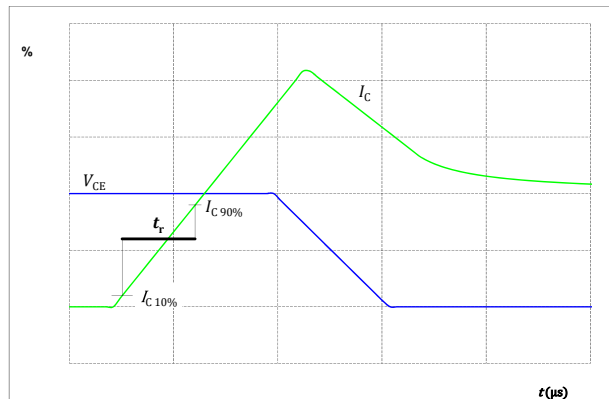


figure 27. IGBT
Turn-on Switching Waveforms & definition of t_r





Inverter Switching Definitions

figure 28. FWD

Turn-off Switching Waveforms & definition of t_{rr}

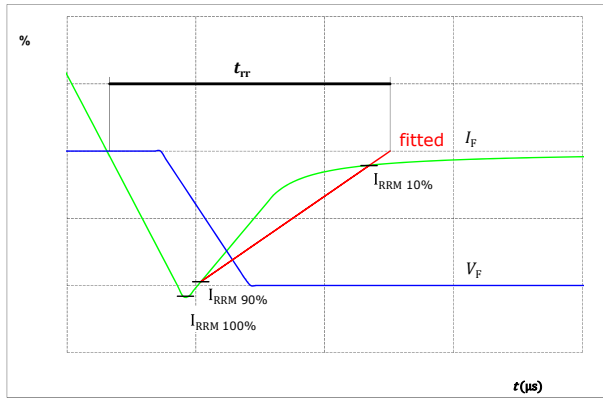
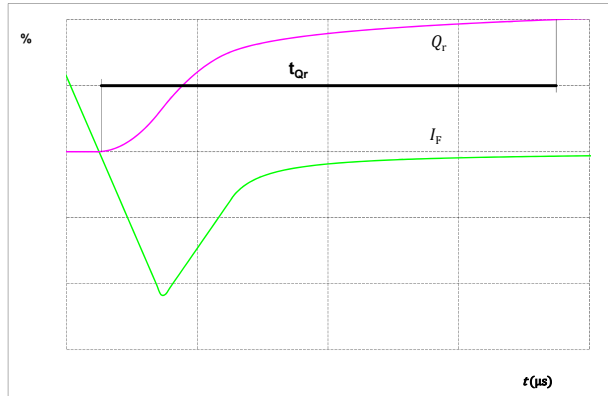


figure 29. FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)






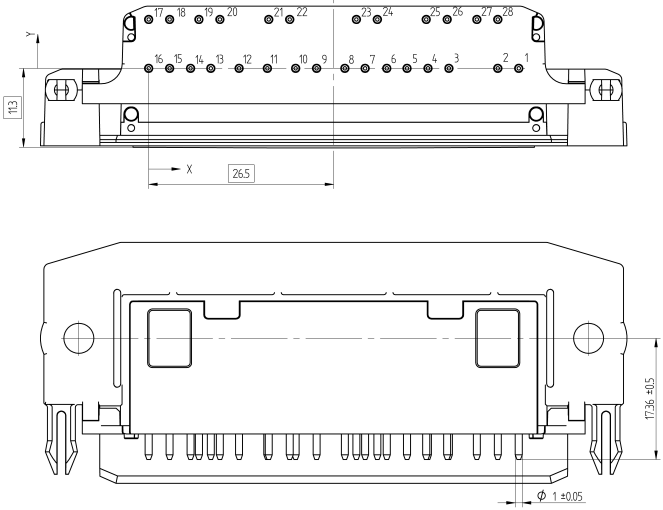
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10-R1126PA015M7-P708F70
datasheet

Ordering Code	
Version	Ordering Code
Without thermal paste	10-R1126PA015M7-P708F70
With thermal paste	10-R1126PA015M7-P708F70-/3/

Marking						
	Text	Name NN-NNNNNNNNNNNNNN- TTTTTVV	Date code WWYY	UL & VIN UL VIN	Lot LLLLL	Serial SSSS
	Datamatrix	Type&Ver TTTTTTVV	Lot number LLLLL	Serial SSSS	Date code WWYY	

Pin table [mm]			
Pin	X	Y	Function
1	53	0	U+
2	50	0	U+
3	43	0	G6
4	40	0	S6
5	37	0	U-
6	34,1	0	U-
7	31	0	U-
8	28,1	0	U-
9	24,05	0	S5
10	21,05	0	G5
11	17	0	G4
12	12,95	0	S4
13	8,9	0	U-
14	6	0	U-
15	3	0	N2
16	0	0	N1
17	0	7	G1
18	3	7	S1
19	7,2	7	U
20	10,2	7	U
21	17,2	7	G2
22	20,2	7	S2
23	29,75	7	V
24	32,75	7	V
25	39,75	7	G3
26	42,75	7	S3
27	47	7	W
28	50	7	W

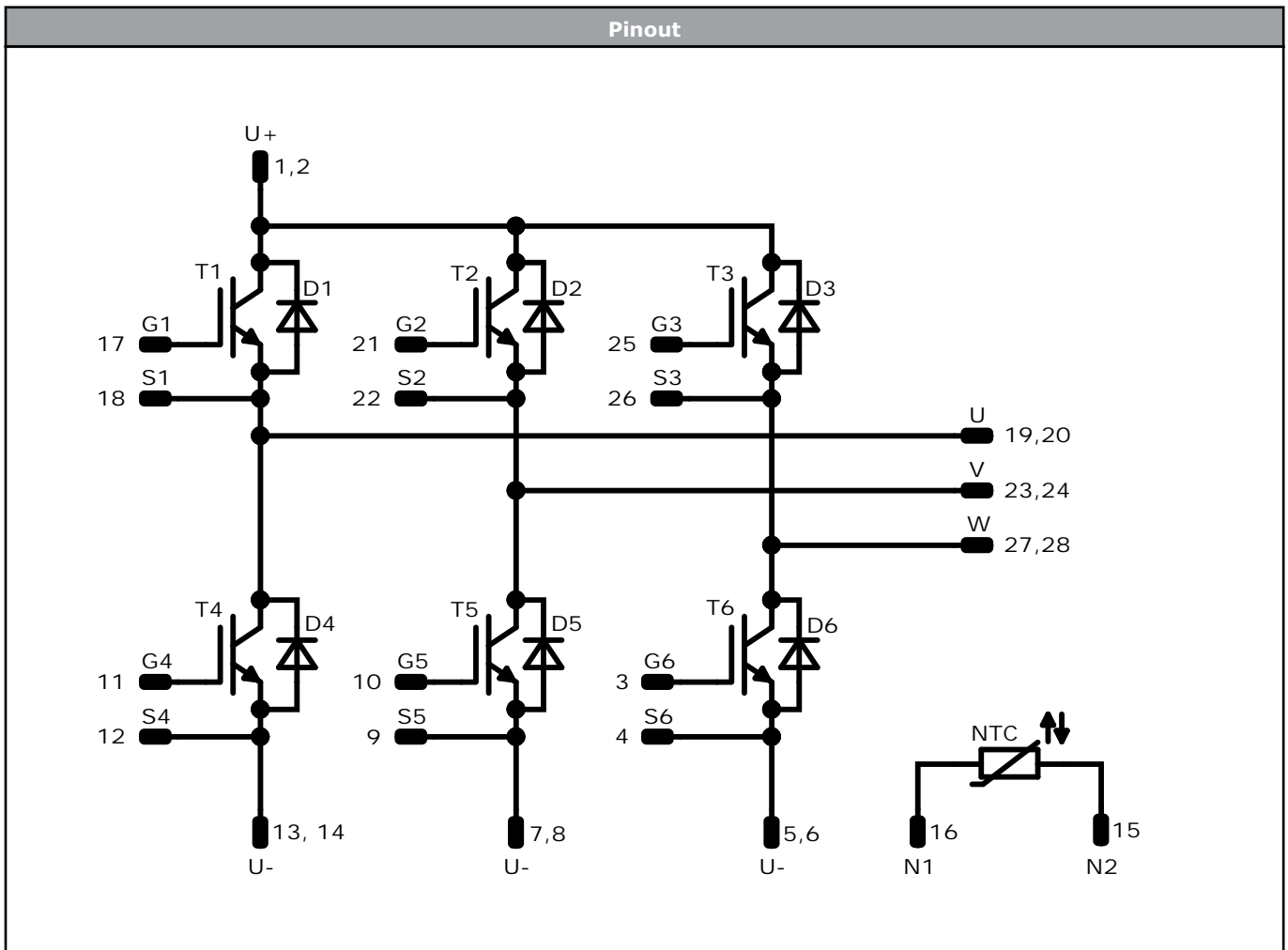


Outline drawing showing top and bottom views of the component. Dimensions include a total length of 265mm, a height of 113mm, and a pin pitch of 17.36 ± 0.05mm. Pin positions are numbered 1 through 28.

Tolerance of pinpositions: ±0.05mm at the end of pins
Dimension of coordinate axis is only offset without tolerance



Vincotech




Identification					
ID	Component	Voltage	Current	Function	Comment
T4, T1, T5, T2, T6, T3	IGBT	1200 V	15 A	Inverter Switch	
D1, D4, D2, D5, D3, D6	FWD	1200 V	15 A	Inverter Diode	
NTC	NTC			Thermistor	



Packaging instruction				
Standard packaging quantity (SPQ) 80	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for <i>flow90</i> 1 packages see vincotech.com website.

Package data
Package data for <i>flow90</i> 1 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website. 

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.